















SN74CB3Q3125

SCDS143C - OCTOBER 2003 - REVISED JUNE 2015

# SN74CB3Q3125 Quadruple FET Bus Switch 2.5-V/3.3-V Low-Voltage, High-Bandwidth Bus Switch

#### **Features**

- High-Bandwidth Data Path (up to 500 MHz<sup>(1)</sup>)
- 5-V Tolerant I/Os With Device Powered Up or Powered Down
- Low and Flat ON-State Resistance (r<sub>on</sub>) Characteristics Over Operating Range  $(r_{on} = 3 \Omega Typ)$
- Rail-to-Rail Switching on Data I/O Ports
  - 0-V to 5-V Switching With 3.3-V V<sub>CC</sub>
  - 0-V to 3.3-V Switching With 2.5-V V<sub>CC</sub>
- Bidirectional Data Flow With Near-Zero **Propagation Delay**
- Low Input and Output Capacitance Minimizes Loading and Signal Distortion  $(C_{io(OFF)} = 4 pF Typ)$
- Fast Switching Frequency ( $f_{OF} = 20 \text{ MHz Max}$ )
- Data and Control Inputs Provide Undershoot Clamp Diodes
- Low Power Consumption  $(I_{CC} = 0.3 \text{ mA Typ})$
- V<sub>CC</sub> Operating Range From 2.3 V to 3.6 V
- Data I/Os Support 0-V to 5-V Signaling Levels (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V, 5 V)
- Control Inputs Can Be Driven by TTL, 5-V, or 3.3-V CMOS Outputs
- Ioff Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
  - 2000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)
- Supports Both Digital and Analog Applications: USB Interface, Differential Signal Interface, Bus Isolation, Low-Distortion Signal Gating
- For additional information regarding the performance characteristics of the CB3Q family, refer to the TI application report, CBT-C, CB3T, and CB3Q Signal-Switch Families (SCDA008).

## 2 Applications

- IP Phones: Wired and Wireless
- **Optical Modules**
- Optical Networking: Video Over Fiber and EPON
- Private Branch Exchange (PBX)
- WiMAX and Wireless Infrastructure Equipment

## 3 Description

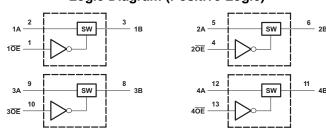
The SN74CB3Q3125 device is a high-bandwidth FET bus switch that uses a charge pump to elevate the gate voltage of the pass transistor, thus providing a low and flat ON-state resistance (ron). The low and ON-state resistance allows for minimal propagation delay and supports rail-to-rail switching the data input/output (I/O) ports. SN74CB3Q3125 device also features low data I/O capacitance to minimize capacitive loading and signal distortion on the data bus.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)	
	VQFN (14)	3.50 mm × 3.50 mm	
SN74CB3Q3125	SSOP (16)	4.90 mm × 3.90 mm	
SN/4CB3Q3125	TSSOP (16)	5.00 mm × 4.40 mm	
	TVSOP (16)	4.40 mm × 3.60 mm	

(1) For all available packages, see the orderable addendum at the end of the data sheet.

### Logic Diagram (Positive Logic)



Pin numbers shown are for the DGV, PW, and RGY packages.



### **Table of Contents**

1	Features 1		8.3 Feature Description	9
2	Applications 1		8.4 Device Functional Modes	9
3	Description 1	9	Application and Implementation	10
4	Revision History2		9.1 Application Information	10
5	Pin Configuration and Functions3		9.2 Typical Application	10
6	Specifications4	10	Power Supply Recommendations	11
U	6.1 Absolute Maximum Ratings	11	Layout	12
	6.2 ESD Ratings		11.1 Layout Guidelines	12
	6.3 Recommended Operating Conditions		11.2 Layout Example	12
	6.4 Thermal Information	12	Device and Documentation Support	13
	6.5 Electrical Characteristics		12.1 Documentation Support	13
	6.6 Switching Characteristics		12.2 Community Resources	13
	6.7 Typical Characteristics		12.3 Trademarks	13
7	Parameter Measurement Information 7		12.4 Electrostatic Discharge Caution	13
8	Detailed Description 8		12.5 Glossary	13
-	8.1 Overview	13	Mechanical, Packaging, and Orderable Information	13
	č			

### 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

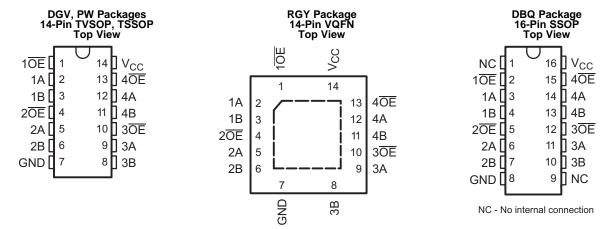
### Changes from Revision B (March 2005) to Revision C

**Page** 

Submit Documentation Feedback



## 5 Pin Configuration and Functions



**Pin Functions** 

	PIN			
NAME	DGV, PW, RGY	DBQ	I/O	DESCRIPTION
1 <del>OE</del>	1	2	I	Output Enable (Active Low)
1A	2	3	I/O	Channel 1A I/O 1A
1B	3	4	I/O	Channel 1B I/O 1B
2 <del>OE</del>	4	5	I	Output Enable (Active Low)
2A	5	6	I/O	Channel 2A I/O 2A
2B	6	7	I/O	Channel 2B I/O 2B
GND	7	8	_	Ground
3B	8	10	I/O	Channel 3B I/O 3B
3A	9	11	I/O	Channel 3A I/O 3B
3 <del>OE</del>	10	12	I	Output Enable (Active Low)
4B	11	13	I/O	Channel 4B I/O 4B
4A	12	14	I/O	Channel 4A I/O 4B
4 <del>OE</del>	13	15	I	Output Enable (Active Low)
NC	_	1, 9	_	No Connect
V <sub>CC</sub>	14	16	_	Power



## 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

				MIN	MAX	UNIT
$V_{CC}$	Supply voltage			-0.5	4.6	V
V <sub>IN</sub>	Control input voltage <sup>(2)(3)</sup>				7	V
V <sub>I/O</sub>	Switch I/O voltage <sup>(2)(3)(4)</sup>		-0.5	7	V	
I <sub>I/K</sub>	Control input clamp current	V <sub>IN</sub> < 0			<b>-</b> 50	mA
I <sub>I/OK</sub>	I/O port clamp current	V <sub>I/O</sub> < 0			<b>-</b> 50	mA
I <sub>IO</sub>	ON-state switch current <sup>(5)</sup>				±64	mA
	Continuous current through V <sub>CC</sub> or GND				±100	mA
T <sub>J</sub>	Junction temperature				150	°C
T <sub>stg</sub>	Storage temperature			-65	150	

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to ground, unless otherwise specified.

### 6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	+2000	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	+1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

#### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage		2.3	3.6	V
\/	High level central input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		5.5	V
V <sub>IH</sub>	High-level control input voltage	2	5.5	V	
\/	Low lovel control input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V
$V_{IL}$	Low-level control input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	0	0.8	V
$V_{I/O}$	Data input and output voltage		0	5.5	V
T <sub>A</sub>	Operating free-air temperature		-40	85	°C

All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs (SCBA004).

#### 6.4 Thermal Information

		SN74CB3Q3257						
	THERMAL METRIC <sup>(1)</sup>	DBQ (SSOP)	DGV (TVSOP)	PW (TSSOP)	RGY (VQFN)	UNIT		
		16 PINS	14 PINS	14 PINS	14 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	90	127	113	47	°C/W		

 For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

<sup>(3)</sup> The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

<sup>(4)</sup>  $V_I$  and  $V_O$  are used to denote specific conditions for  $V_{I/O}$ .

<sup>(5)</sup> I<sub>I</sub> and I<sub>O</sub> are used to denote specific conditions for I<sub>I/O</sub>.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



#### 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)(1)

PA	RAMETER		TEST CONDITION	S	MIN	TYP <sup>(2)</sup>	MAX	UNIT
V <sub>IK</sub>		V <sub>CC</sub> = 3.6 V,	I <sub>I</sub> = -18 mA				-1.8	V
I <sub>IN</sub>	Control inputs	$V_{CC} = 3.6 \text{ V},$	$V_{IN} = 0 \text{ to } 5.5 \text{ V}$				±1	μΑ
I <sub>OZ</sub> <sup>(3)</sup>		V <sub>CC</sub> = 3.6 V,	$V_O = 0 \text{ to } 5.5 \text{ V},$ $V_I = 0,$	Switch OFF, V <sub>IN</sub> = V <sub>CC</sub> or GND			±1	μΑ
I <sub>off</sub>		$V_{CC} = 0$ ,	$V_0 = 0 \text{ to } 5.5 \text{ V},$	V <sub>I</sub> = 0			1	μA
I <sub>CC</sub>		V <sub>CC</sub> = 3.6 V,	$I_{I/O} = 0$ , Switch ON or OFF,	$V_{IN} = V_{CC}$ or GND		0.3	1	mA
$\Delta I_{CC}^{(4)}$	Control inputs	V <sub>CC</sub> = 3.6 V,	One input at 3 V,	Other inputs at V <sub>CC</sub> or GND			30	μA
, (5) Per control	V <sub>CC</sub> = 3.6 V,	A and B ports open,			0.04	0.2	mA/	
I <sub>CCD</sub> <sup>(5)</sup>	input	Control input switching	0.0	0.04	0.2	MHz		
C <sub>in</sub>	Control inputs	V <sub>CC</sub> = 3.3 V,	V <sub>IN</sub> = 5.5 V, 3.3 V, or 0			2.5	3.5	pF
C <sub>io(OFF)</sub>		V <sub>CC</sub> = 3.3 V,	Switch OFF, $V_{IN} = V_{CC}$ or GND,	$V_{I/O} = 5.5 \text{ V}, 3.3 \text{ V}, \text{ or } 0$		4	5	pF
C <sub>io(ON)</sub>		V <sub>CC</sub> = 3.3 V,	Switch ON, $V_{IN} = V_{CC}$ or GND,	$V_{I/O} = 5.5 \text{ V}, 3.3 \text{ V}, \text{ or } 0$		8	10	pF
		$V_{CC} = 2.3 \text{ V},$	$V_I = 0$ ,	$I_O = 30 \text{ mA}$		4	8	
r <sub>on</sub> (6)		TYP at $V_{CC} = 2.5 \text{ V}$	V <sub>I</sub> = 1.7 V,	I <sub>O</sub> = -15 mA		4	9	0
Ion `'		\\\ - 2 \\	$V_I = 0$ ,	I <sub>O</sub> = 30 mA		4	6	Ω
		$V_{CC} = 3 V$	$V_1 = 2.4 V,$	$I_O = -15 \text{ mA}$		4	8	

- $V_{IN}$  and  $I_{IN}$  refer to control inputs.  $V_{I},\ V_{O},\ I_{I},$  and  $I_{O}$  refer to data pins. All typical values are at  $V_{CC}$  = 3.3 V (unless otherwise noted),  $T_{A}$  = 25°C.
- For I/O ports, the parameter I<sub>OZ</sub> includes the input leakage current.
- This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V<sub>CC</sub> or GND.
- This parameter specifies the dynamic power-supply current associated with the operating frequency of a single control input (see Figure 2).
- Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

### 6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

DADAMETED	FROM	то	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$		V <sub>CC</sub> = 3.3 V ±	UNIT	
PARAMETER	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	UNII
f OE (1)	ŌĒ	A or B		10		20	MHz
$t_{pd}^{(2)}$	A or B	B or A		0.12		0.2	ns
t <sub>en</sub>	ŌĒ	A or B	1.5	6.7	1.5	6.6	ns
t <sub>dis</sub>	ŌĒ	A or B	1	4.6	1	5.3	ns

Maximum switching frequency for control input ( $V_O > V_{CC}$ ,  $V_I = 5$  V,  $R_L \ge 1$  M $\Omega$ ,  $C_L = 0$ ) The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).



## 6.7 Typical Characteristics

At  $T_A = 25^{\circ}\text{C}$  and  $V_{\text{CC}} = 3.3 \text{ V}$ , unless otherwise noted.

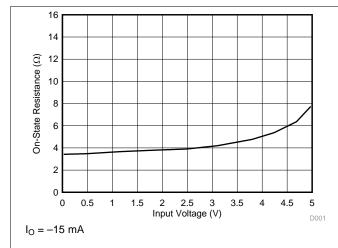


Figure 1. Typical On-State Resistance vs Input Voltage

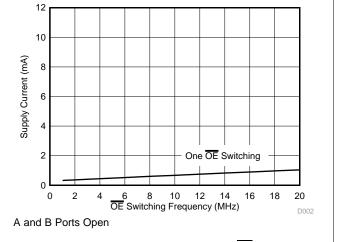


Figure 2. Typical Supply Current vs  $\overline{\text{OE}}$  Switching Frequency

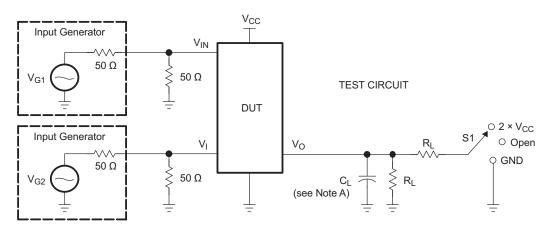
Submit Documentation Feedback

Copyright © 2003–2015, Texas Instruments Incorporated

 $V_{\text{CC}}$ 

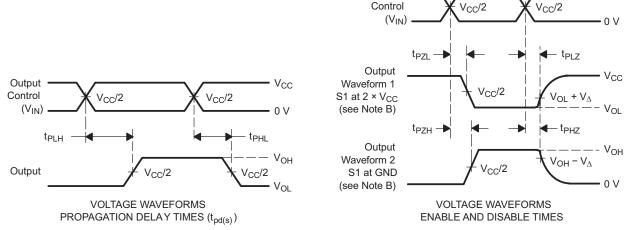


### 7 Parameter Measurement Information



TEST	V <sub>CC</sub>	S1	$R_L$	V <sub>I</sub>	C <sub>L</sub>	$V_{\Delta}$
t <sub>pd(s)</sub>	2.5 V ± 0.2 V 3.3 V ± 0.3 V	Open Open	500 Ω 500 Ω	V <sub>CC</sub> or GND V <sub>CC</sub> or GND	30 pF 50 pF	
t <sub>PLZ</sub> /t <sub>PZL</sub>	2.5 V ± 0.2 V 3.3 V ± 0.3 V	2 × V <sub>CC</sub> 2 × V <sub>CC</sub>	500 Ω 500 Ω	GND GND	30 pF 50 pF	0.15 V 0.3 V
t <sub>PHZ</sub> /t <sub>PZH</sub>	2.5 V ± 0.2 V 3.3 V ± 0.3 V	GND GND	500 Ω 500 Ω	V <sub>CC</sub>	30 pF 50 pF	0.15 V 0.3 V

Output



- A. C<sub>L</sub> includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$ 10 MHz,  $Z_O = 50 \Omega$ ,  $t_r \leq$ 2.5 ns,  $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t<sub>PLZ</sub> and t<sub>PHZ</sub> are the same as t<sub>dis</sub>.
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as ten.
- G. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>pd(s)</sub>. The t<sub>pd</sub> propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Test Circuit and Voltage Waveforms

Submit Documentation Feedback



### 8 Detailed Description

#### 8.1 Overview

The SN74CB3Q3125 device is a high-bandwidth FET bus switch utilizing a charge pump to elevate the gate voltage of the pass transistor, providing a low and flat ON-state resistance (r<sub>on</sub>). The low and flat ON-state resistance allows for minimal propagation delay and supports rail-to-rail switching on the data input/output (I/O) ports. The SN74CB3Q3125 device also features low data I/O capacitance to minimize capacitive loading and signal distortion on the data bus. Specifically designed to support high-bandwidth applications, the SN74CB3Q3125 device provides an optimized interface solution ideally suited for broadband communications, networking, and data-intensive computing systems.

The SN74CB3Q3125 device is organized as four 1-bit bus switches with separate output-enable  $(1\overline{OE}, 2\overline{OE}, 3\overline{OE}, 4\overline{OE})$  inputs. It can be used as four 1-bit bus switches or as one 4-bit bus switch. When  $\overline{OE}$  is low, the associated 1-bit bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When  $\overline{OE}$  is high, the associated 1-bit bus switch is OFF, and a high-impedance state exists between the A and B ports.

This device is fully specified for partial-power-down applications using I<sub>off</sub>. The I<sub>off</sub> circuitry prevents damaging current backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

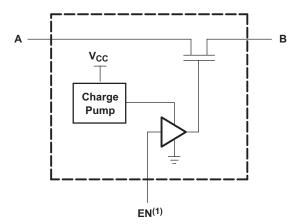
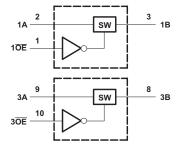
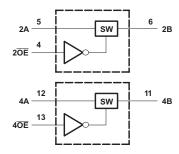


Figure 4. Simplified Schematic, Each FET Switch (SW)

#### 8.2 Functional Block Diagram





Submit Documentation Feedback

Copyright © 2003–2015, Texas Instruments Incorporated



#### 8.3 Feature Description

The SN74CB3Q3125 device has a high-bandwidth data path (up to 500 MHz) and has 5-V tolerant I/Os with the device powered up or powered down. It also has low and flat ON-state resistance ( $r_{on}$ ) characteristics over operating range ( $r_{on} = 4-\Omega$  Typ).

The SN74CB3Q3125 device has rail-to-rail switching on data I/O ports for 0-V to 5-V switching with 3.3-V  $V_{CC}$  and 0-V to 3.3-V switching with 2.5-V  $V_{CC}$  as well as bidirectional data flow with near-zero propagation delay and low input/output capacitance that minimizes loading and signal distortion ( $C_{Io(OFF)} = 3.5$ -pF Typ).

The SN74CB3Q3125 device also provides a fast switching frequency ( $f_{\overline{OE}} = 20$ -MHz Max) with data and control inputs that provide undershoot clamp diodes as well as low power consumption ( $I_{CC} = 0.6$ -mA Typ).

The  $V_{CC}$  operating range is from 2.3 V to 3.6 V and the data I/Os support 0-V to 5-V signal levels of (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V, 5 V).

The control inputs can be driven by TTL or 5-V or 3.3-V CMOS outputs, and I<sub>off</sub> supports partial-power-down mode operation.

#### 8.4 Device Functional Modes

Table 1 lists the functional modes for the SN74CB3Q3125 device.

**Table 1. Function Table** 

INPUT OE	INPUT/OUTPUT A	FUNCTION
L	В	A port = B port
Н	Z	Disconnect



### 9 Application and Implementation

#### NOTE

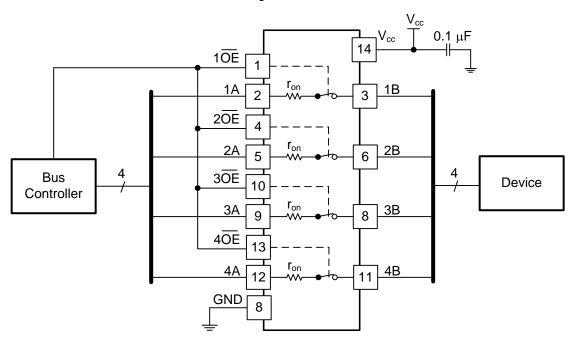
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

The SN74CB3Q3125 device can be used to control up to four channels simultaneously.

### 9.2 Typical Application

The application shown in Figure 5 is a 4-bit bus being controlled. The  $\overline{OE}$  pins are used to control the chip from the bus controller. This is a very generic example and can apply to many situations. If an application requires less than 4 bits, be sure to tie the A side to either high or low on unused channels.



Pin numbers for DGV, PW, RGY packages only

Figure 5. Typical Application of the SN74CB3Q3257

#### 9.2.1 Design Requirements

The 0.1-μF capacitor must be placed as close as possible to the SN74CB3Q3257 device.

Submit Documentation Feedback



### **Typical Application (continued)**

#### 9.2.2 Detailed Design Procedure

- 1. Recommended input conditions:
  - For specified high and low levels, see V<sub>IH</sub> and V<sub>IL</sub> in Recommended Operating Conditions
  - Inputs and outputs are overvoltage tolerant, which slows them to go as high as 5.5 V at any valid V<sub>CC</sub>
- 2. Recommended output conditions:
  - Load currents must not exceed ±64 mA per channel
- 3. Frequency selection criterion:
  - Added trace resistance or capacitance can reduce maximum frequency capability; use layout practices as directed in *Layout*

#### 9.2.3 Application Curve

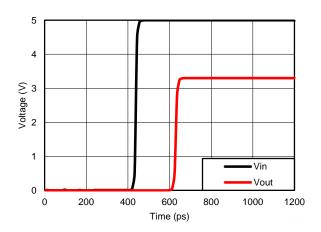


Figure 6. Propagation Delay  $(t_{pd})$  Simulation Result at  $V_{CC} = 3.3 \text{ V}$ 

### 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Absolute Maximum Ratings* table.

Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu$ F bypass capacitor is recommended. If multiple pins are labeled  $V_{CC}$ , then a 0.01- $\mu$ F or 0.022- $\mu$ F capacitor is recommended for each  $V_{CC}$  because the  $V_{CC}$  pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example  $V_{CC}$  and  $V_{DD}$ , a 0.1- $\mu$ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1  $\mu$ F and 1  $\mu$ F are commonly used in parallel. The bypass capacitor must be installed as close to the power terminal as possible for best results.



## 11 Layout

#### 11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace, which results in the reflection. Not all PCB traces can be straight; therefore, some traces must turn corners. Figure 7 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

#### 11.2 Layout Example

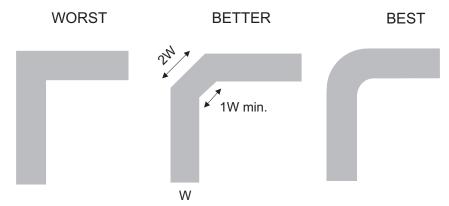


Figure 7. Trace Example

Submit Documentation Feedback



## 12 Device and Documentation Support

### 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation see the following:

- Implications of Slow or Floating CMOS Inputs, SCBA004
- Selecting the Right Texas Instruments Signal Switch, SZZA030

### 12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community T's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.3 Trademarks

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

### 12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Copyright © 2003–2015, Texas Instruments Incorporated

www.ti.com 6-Jan-2025

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	( - )				_	(=/	(6)	(4)		()	
SN74CB3Q3125DBQR	ACTIVE	SSOP	DBQ	16	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU125	Samples
SN74CB3Q3125DGVR	ACTIVE	TVSOP	DGV	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU125	Samples
SN74CB3Q3125PW	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI	-40 to 85	BU125	
SN74CB3Q3125PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU125	Samples
SN74CB3Q3125RGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU125	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and



## **PACKAGE OPTION ADDENDUM**

www.ti.com 6-Jan-2025

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## **PACKAGE MATERIALS INFORMATION**

www.ti.com 14-Dec-2024

### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3Q3125DBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN74CB3Q3125DGVR	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3Q3125PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CB3Q3125RGYR	VQFN	RGY	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1



www.ti.com 14-Dec-2024



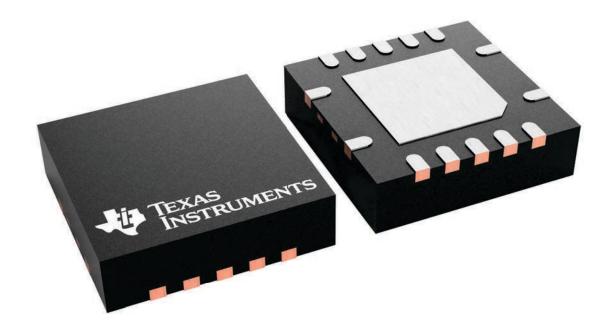
#### \*All dimensions are nominal

7 ill difference die flerima.										
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)			
SN74CB3Q3125DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0			
SN74CB3Q3125DGVR	TVSOP	DGV	14	2000	367.0	367.0	35.0			
SN74CB3Q3125PWR	TSSOP	PW	14	2000	367.0	367.0	35.0			
SN74CB3Q3125RGYR	VQFN	RGY	14	3000	367.0	367.0	35.0			

3.5 x 3.5, 0.5 mm pitch

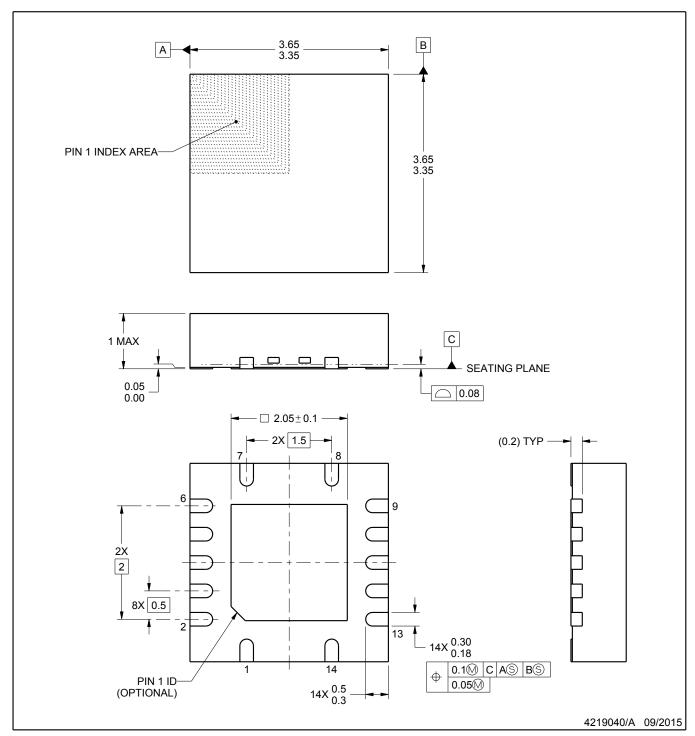
PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





PLASTIC QUAD FLATPACK - NO LEAD

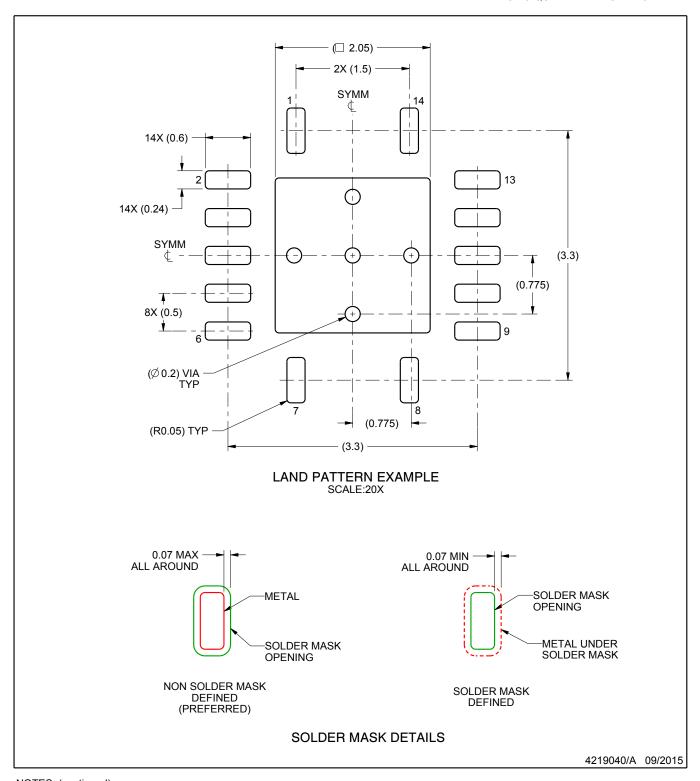


#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
   The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

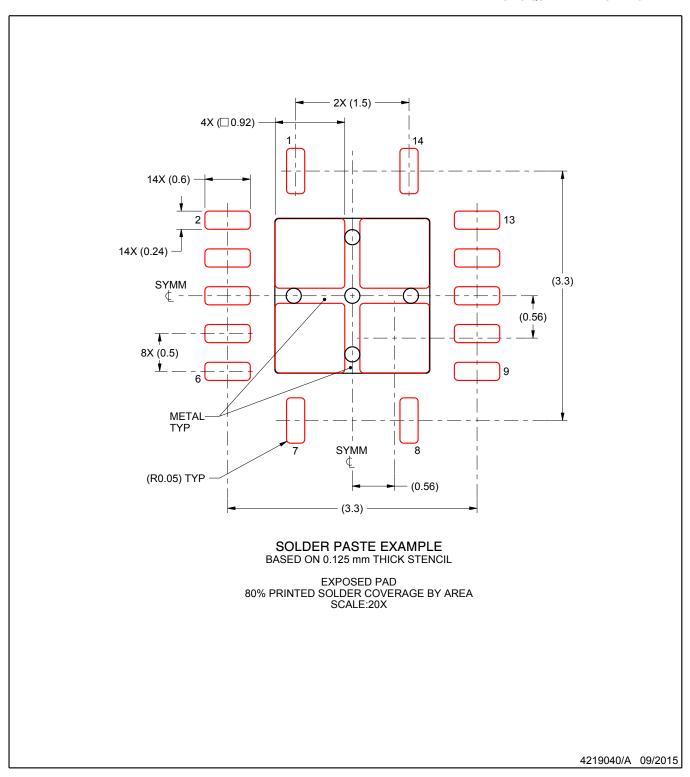


NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



## DGV (R-PDSO-G\*\*)

#### **24 PINS SHOWN**

#### **PLASTIC SMALL-OUTLINE**



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.

D. Falls within JEDEC: 24/48 Pins – MO-153 14/16/20/56 Pins – MO-194



SHRINK SMALL-OUTLINE PACKAGE



### NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MO-137, variation AB.



SHRINK SMALL-OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SHRINK SMALL-OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE PACKAGE



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



#### IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025. Texas Instruments Incorporated